-5 V Differential ECL to TTL Translator

MC10ELT25, MC100ELT25

Description

The MC10ELT/100ELT25 is a differential ECL to TTL translator. Because ECL levels are used, a +5 V, -5.2 V (or -4.5 V) and ground are required. The small outline 8-lead package and the single gate of the ELT25 makes it ideal for those applications where space, performance and low power are at a premium.

The V_{BB} pin, an internally generated voltage supply, is available to this device only. For single-ended input conditions, the unused differential input is connected to V_{BB} as a switching reference voltage. V_{BB} may also rebias AC coupled inputs. When used, decouple V_{BB} and V_{CC} via a $0.01~\mu F$ capacitor and limit current sourcing or sinking to 0.5~mA. When not used, V_{BB} should be left open.

The 100 Series contains temperature compensation.

Features

- 2.6 ns Typical Propagation Delay
- 100 MHz F_{MAX} CLK
- 24 mA TTL Outputs
- Flow Through Pinouts
- Operating Range: $V_{CC} = 4.5 \text{ V}$ to 5.5 V with GND = 0 V; $V_{EE} = -4.2 \text{ V}$ to -5.7 V with GND = 0 V
- Internal Input 50 kΩ Pulldown Resistors
- Q Output will default HIGH with inputs open or < 1.3 V
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



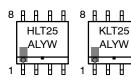
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MARKING DIAGRAMS*



SOIC-8 D SUFFIX CASE 751





TSSOP-8 DT SUFFIX CASE 948R



H = MC10 K = MC100

A = Assembly Location

L = Wafer Lot Y = Year W = Work Week • = Pb-Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note <u>AND8002/D</u>.

ORDERING INFORMATION

Device	Package	Shipping [†]
MC10ELT25DG	SOIC-8 (Pb-Free)	98 Units / Tube
MC10ELT25DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC100ELT25DG	SOIC-8 (Pb-Free)	98 Units / Tube
MC100ELT25DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC100ELT25DTG	TSSOP-8 (Pb-Free)	100 Units / Tube

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

MC10ELT25, MC100ELT25

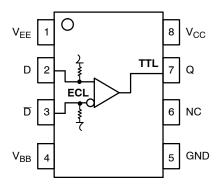


Figure 1. 8-Lead Pinout (Top View) and Logic Diagram

Table 1. PIN DESCRIPTION

Pin	Function	
D, \overline{D}	ECL Differential Inputs	
Q	TTL Output	
V_{BB}	Reference Voltage Output	
V _{CC}	Positive Supply	
V _{EE}	Negative Supply	
GND	Ground	
NC	No Connect	

Table 2. ATTRIBUTES

Characteristics	Value
Internal Input Pulldown Resistor	75 kΩ
Internal Input Pullup Resistor	N/A
ESD Protection Human Body Model Machine Model	> 1 kV > 400 V
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC-8 TSSOP-8	Level 1 Level 3
Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in
Transistor Count	38 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	•

^{1.} For additional information, see Application Note AND8003/D.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V _{CC}	Positive Power Supply	GND = 0 V	V _{EE} = -5.0 V	7	V
V _{EE}	Negative Power Supply	GND = 0 V	V _{CC} = +5.0 V	-8	V
V _{IN}	Input Voltage	GND = 0 V		0 to V _{EE}	V
I _{BB}	V _{BB} Sink/Source			±0.5	mA
T _A	Operating Temperature Range			-40 to +85	°C
T _{stg}	Storage Temperature Range			-65 to +150	°C
$\theta_{\sf JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 SOIC-8	190 130	°C/W °C/W
θJC	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP-8 TSSOP-8	185 140	°C/W °C/W
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44 ±5%	°C/W
T _{sol}	Wave Solder Pb-Free	<2 to 3 sec @ 260°C		265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. JEDEC standard multilayer board – 2S2P (2 signal, 2 power)

MC10ELT25, MC100ELT25

Table 4. 10ELT SERIES NECL INPUT DC CHARACTERISTICS $V_{CC} = 5.0 \text{ V}$; $V_{EE} = -5.0 \text{ V}$; GND = 0 V (Note 3)

		-40°C		25°C			85°C				
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
V _{IH}	Input HIGH Voltage (Single-Ended) (Note 4)	-1230		-890	-1130		-810	-1060		-720	mV
V _{IL}	Input LOW Voltage (Single-Ended) (Note 4)	-1950		-1500	-1950		-1480	-1950		-1445	mV
V _{BB}	Output Voltage Reference	-1.43		-1.30	-1.35		-1.25	-1.31		-1.19	V
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential) (Notes 4 and 5)	-2.8		0.0	-2.8		0.0	-2.8		0.0	٧
I _{IH}	Input HIGH Current			255			175			175	μΑ
I _{IL}	Input LOW Current	0.5			0.5			0.3			μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

- 3. Input parameters vary 1:1 with GND. V_{EE} can vary +0.06 V to -0.5 V.
- 4. TTL output $R_L = 500 \Omega$ to GND
- 5. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with GND.

Table 5. 100ELT SERIES NECL INPUT DC CHARACTERISTICS $V_{CC} = 5.0 \text{ V}$; $V_{EE} = -5.0 \text{ V}$; GND = 0 V (Note 6)

		-40°C		25°C		85°C					
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
V _{IH}	Input HIGH Voltage (Single-Ended) (Note 7)	-1165		-880	-1165		-880	-1165		-880	mV
V _{IL}	Input LOW Voltage (Single-Ended) (Note 7)	-1810		-1475	-1810		-1475	-1810		-1475	mV
V _{BB}	Output Voltage Reference	-1.38		-1.26	-1.38		-1.26	-1.38		-1.26	٧
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential) (Notes 7 and 8)	-2.8		0.0	-2.8		0.0	-2.8		0.0	٧
I _{IH}	Input HIGH Current			255			175			175	μΑ
I _{IL}	Input LOW Current	0.5			0.5			0.5			μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

- 6. Input parameters vary 1:1 with GND. V_{EE} can vary +0.8 V to -0.5 V.
- 7. TTL output R_L = 500 Ω to GND
- 8. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with GND.

Table 6. TTL OUTPUT DC CHARACTERISTICS V_{CC} = 4.5 V to 5.5 V; T_A = -40°C to +85°C

Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V _{OH}	Output HIGH Voltage	I _{OH} = -3.0 mA	2.4			V
V _{OL}	Output LOW Voltage	I _{OL} = 24 mA			0.5	V
I _{CCH}	Power Supply Current			11	16	mA
I _{CCL}	Power Supply Current			13	18	mA
I _{EE}	Negative Power Supply Current			15	21	mA
I _{OS}	Output Short Circuit Current		-150		-60	mA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

MC10ELT25, MC100ELT25

Table 7. AC CHARACTERISTICS V_{CC}= 5.0 V; V_{EE}= -5.0 V; GND= 0 V (Note 9 and Note 10)

		-40°C		25°C			85°C				
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f _{max}	Maximum Toggle Frequency					100					MHz
t _{PLH}	Propagation Delay @ 1.5 V	1.7		3.6	1.7		3.6	1.7		3.6	ns
t _{PHL}	Propagation Delay @ 1.5 V	2.6		4.1	2.6		4.1	2.6		4.1	ns
t _{JITTER}	Random Clock Jitter (RMS)					35					ps
t _r t _f	Output Rise/Fall Times QTTL 10% - 90%					1.9 2.3					ns
V _{PP}	Input Swing (Note 11)	200		1000	200		1000	200		1000	mV

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

- 9. V_{CC} can vary \pm 0.25 V.
- V_{EE} can vary +0.06 V to -0.5 V for 10ELT; V_{EE} can vary +0.8 V to -0.5 V for 100ELT.
- 10. R_L = 500 Ω to GND and C_L = 20 pF to GND. Refer to Figure 2.
- 11. $V_{PP}(min)$ is the minimum input swing for which AC parameters are guaranteed. The device has a DC gain of \approx 40.

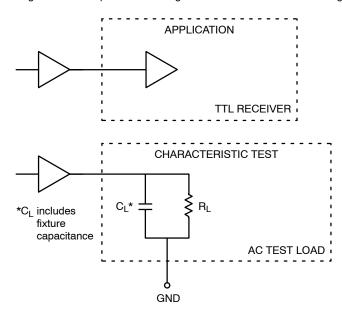


Figure 2. TTL Output Loading Used for Device Evaluation

Resource Reference of Application Notes

AN1405/D - ECL Clock Distribution Techniques

AN1406/D - Designing with PECL (ECL at +5.0 V)

AN1503/D - ECLinPS™ I/O SPiCE Modeling Kit

AN1504/D - Metastability and the ECLinPS Family

Marking and Date Codes

AN1568/D - Interfacing Between LVDS and ECL

AN1672/D – The ECL Translator Guide

AND8001/D – Odd Number Counters Design

AND8020/D - Termination of ECL Logic Devices

AND8066/D - Interfacing with ECLinPS

AND8002/D

AND8090/D - AC Characteristics of ECL Devices

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SOIC-8 NB CASE 751-07 **ISSUE AK**

DATE 16 FEB 2011



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27	7 BSC	0.05	0 BSC	
Н	0.10	0.25	0.004	0.010	
J	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
М	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

= Wafer Lot = Year = Work Week

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww = Work Week

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SOIC-8 NB CASE 751-07 ISSUE AK

DATE 16 FEB 2011

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1 STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. PINS 2	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1 STYLE 7: PIN 1. IMPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2	3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE 2. SOURCE
PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND	PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2	PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE 2. SOURCE
PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND	PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2	PIN 1. SOURCE 2. SOURCE
6. BIAS 2 7. INPUT 8. GROUND	5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		
	PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE 8. CATHODE 8. CATHODE 8. CATHODE 8. CATHODE 9. COMMON CATHODE/VCC 9. COMMON CATHODE/VCC 1. I/O LINE 1 2. COMMON CATHODE/VCC 1. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 5 8. COMMON ANODE/GND 8. COMMON ANODE/GND 8. COMMON ANODE/GND 8. COMMON ANODE/GND 8. I/O LINE 5 8. COMMON ANODE/GND 8. SOURCE 9. I/O LINE 5 8. COMMON ANODE/GND 8. VILLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILLIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC 8. VCC 8. VCC 8. VCC 8. VCC 8. SOURCE 2 4. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2	PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 7. CATHODE, COMMON 8. N-DRAIN 8. CATHODE, COMMON 8. CATHODE 9IN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 4. GATE 2 5. DRAIN 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1 8. COMMON CATHODE/VCC 1. COMMON CATHODE/VCC 1. COMMON CATHODE/VCC 1. (/O LINE 1 2. COMMON CATHODE/VCC 1. (/O LINE 3 5. COMMON ANODE/GND 6. (/O LINE 4 7. (/O LINE 5 8. COMMON ANODE/GND 8. LINE 2 OUT 9. COMMON ANODE/GND 8. LINE 1 OUT STYLE 26: PIN 1. GND 9. LINE 2 OUT 9. COMMON ANODE/GND 9. LINE 1 OUT STYLE 27: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 1 OUT STYLE 28: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 1 OUT STYLE 29: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 1 OUT STYLE 29: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 2 OUT 9. COMMON ANODE/GND 9. LINE 1 OUT STYLE 29: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 1 OUT STYLE 29: PIN 1. ILIMIT 9. SOURCE 1/DRAIN 2

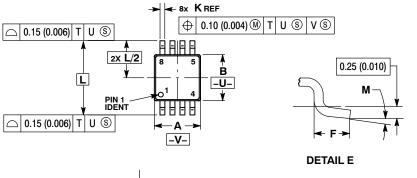
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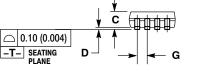
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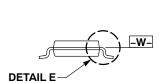


TSSOP 8 CASE 948R-02 ISSUE A

DATE 04/07/2000







- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH. OR GATE BURRS SHALL NOT EXCEED 0.15
- (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
 6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.114	0.122
В	2.90	3.10	0.114	0.122
С	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65	BSC	0.026	BSC
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193 BSC	
M	٥°	6 °	٥°	6°

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